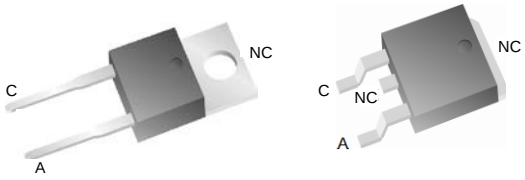
QH03TZ600, QH03BZ600
Qspeed™ Family

600 V, 3 A H-Series PFC Diode

Product Summary

$I_{F(AVG)}$	3	A
V_{RRM}	600	V
Q_{RR} (Typ at 125 °C)	14.8	nC
I_{RRM} (Typ at 125 °C)	1.35	A
Softness t_B/t_A (Typ at 125 °C)	1.1	

Pin Assignment



TO-220AC **QH03TZ600**

TO-263AB **QH03BZ600**

RoHS Compliant

Package uses Lead-free plating and
Green mold compound.
Halogen free per IEC 61249-2-21.

General Description

This device has the lowest Q_{RR} of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

Applications

- Power Factor Correction (PFC) boost diode
- Motor drive circuits
- DC-AC Inverters

Features

- Low Q_{RR}, low I_{RRM}, low t_{RR}
- High dI_F/dt capable (1000 A / µs)
- Soft recovery

Benefits

- Increases efficiency
  - Eliminates need for snubber circuits
  - Reduces EMI filter component size & count
- Enables extremely fast switching

Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Peak repetitive reverse voltage	T_J = 25 °C	600	V
$I_{F(AVG)}$	Average forward current	T_J = 150 °C, T_C = 120 °C	3	A
I_{FSM}	Non-repetitive peak surge current	60 Hz, ½ cycle, T_C = 25 °C	35	A
I_{FSM}	Non-repetitive peak surge current	½ cycle of t = 28 µs Sinusoid, T_C = 25 °C	350	A
T_J	Operating junction temperature range		-55 to 150	°C
T_{STG}	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-220	2500	V
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-263	1500	V
P_D	Power dissipation	T_C = 25 °C	30.4	W

Thermal Resistance

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JA}$	Junction to ambient	TO-220 (only)	62	°C/W
$R_{\theta JC}$	Junction to case		4.1	°C/W

Electrical Specifications at T_J = 25 °C (unless otherwise specified)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
DC Characteristics							
I_R	Reverse current	V_R = 600 V, T_J = 25 °C		-	-	250	µA
		V_R = 600 V, T_J = 125 °C		-	0.22	-	mA
V_F	Forward voltage	I_F = 3 A, T_J = 25 °C		-	2.52	3.0	V
		I_F = 3 A, T_J = 150 °C		-	2.1	-	V
C_J	Junction capacitance	V_R = 10 V, 1 MHz		-	11	-	pF
Dynamic Characteristics							
t_{RR}	Reverse recovery time	dI/dt = 200 A/µs V_R = 400 V, I_F = 3 A	T_J = 25 °C	-	9.8	-	ns
			T_J = 125 °C	-	16.1	-	ns
Q_{RR}	Reverse recovery charge	dI/dt = 200 A/µs V_R = 400 V, I_F = 3 A	T_J = 25 °C	-	5.8	10	nC
			T_J = 125 °C	-	14.8	-	nC
I_{RRM}	Maximum reverse recovery current	dI/dt = 200 A/µs V_R = 400 V, I_F = 3 A	T_J = 25 °C	-	0.93	1.4	A
			T_J = 125 °C	-	1.35	-	A
S	Softness factor = $\frac{t_B}{t_A}$	dI/dt = 200 A/µs V_R = 400 V, I_F = 3 A	T_J = 25 °C	-	0.92	-	
			T_J = 125 °C	-	1.1	-	

Note to component engineers: H-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)

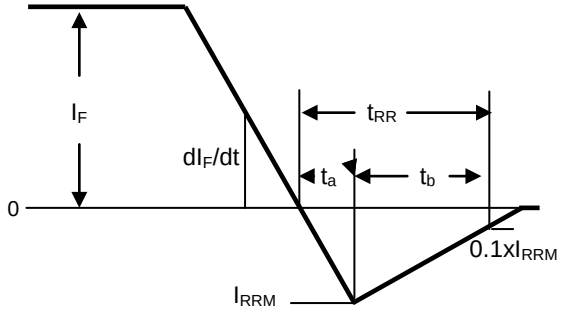


Figure 1. Reverse Recovery Definitions.

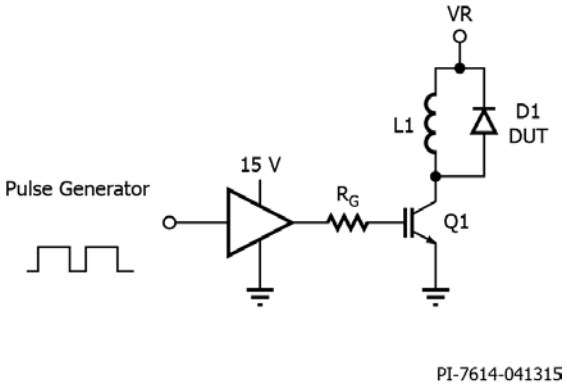


Figure 2. Reverse Recovery Test Circuit.

Electrical Specifications at T_J = 25 °C (unless otherwise specified)

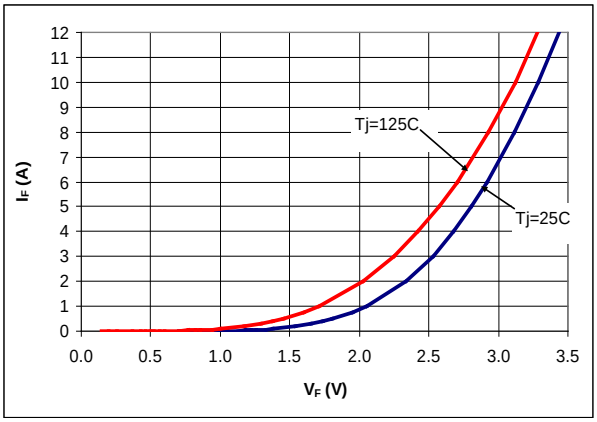


Figure 3. Typical I_F vs. V_F.

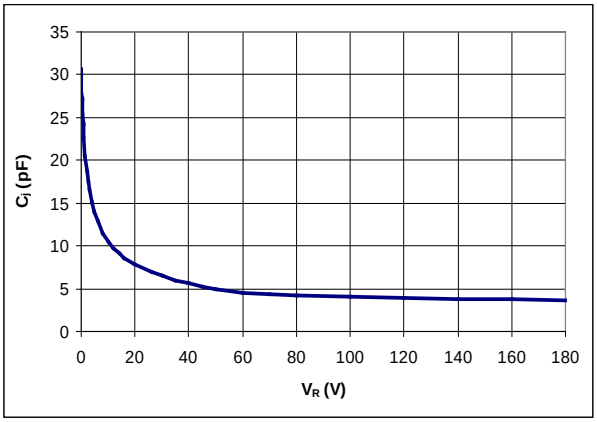


Figure 4. Typical C_J vs V_R.

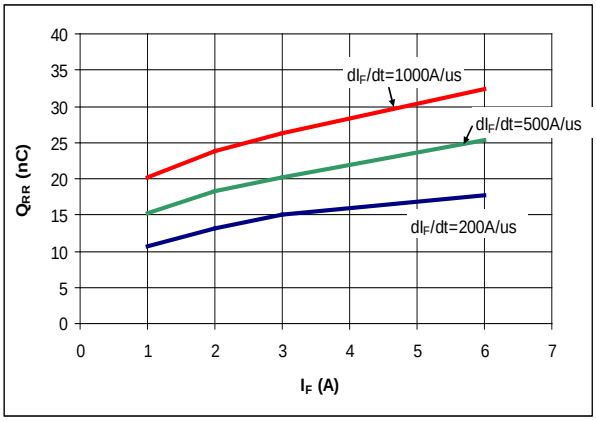


Figure 5. Typical Q_{RR} vs. I_F at T_J = 125 °C.

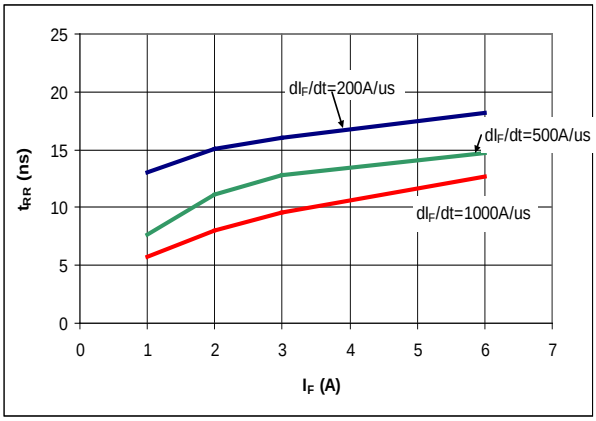


Figure 6. Typical t_{RR} vs. I_F at T_J = 125 °C.

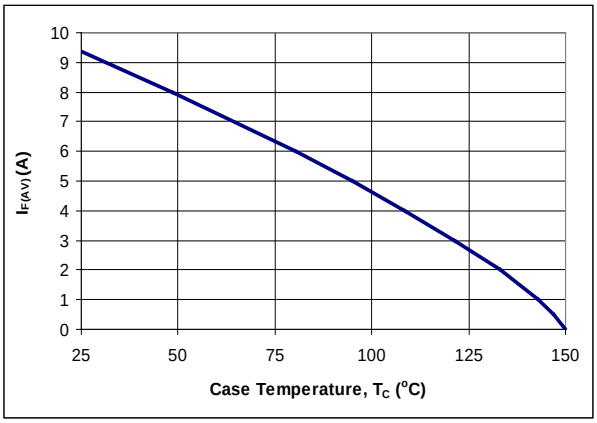


Figure 7. DC Current Derating Curve.

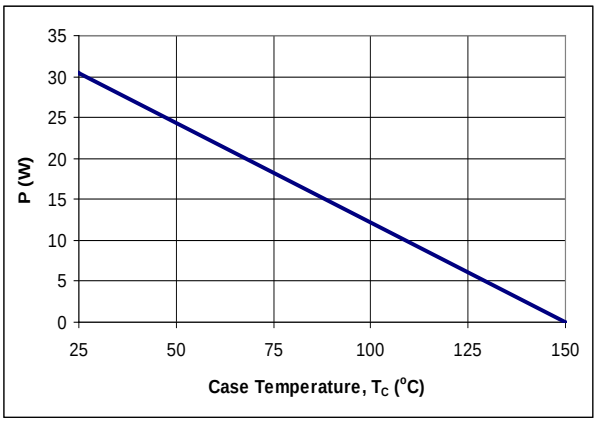


Figure 8. Power Derating Curve.

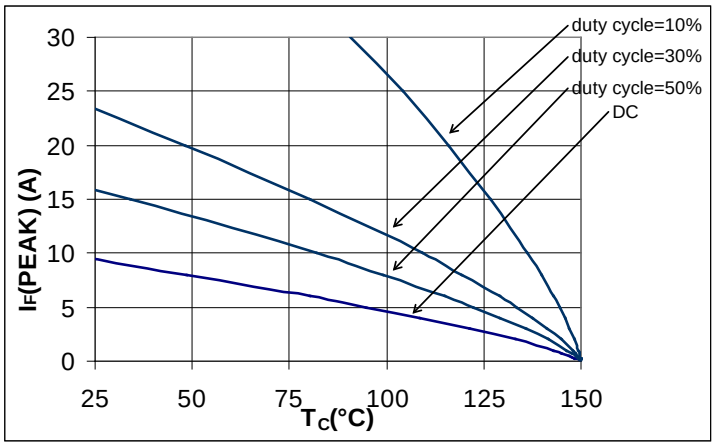


Figure 9. I_F(PEAK) vs. T_C, f = 70 kHz.

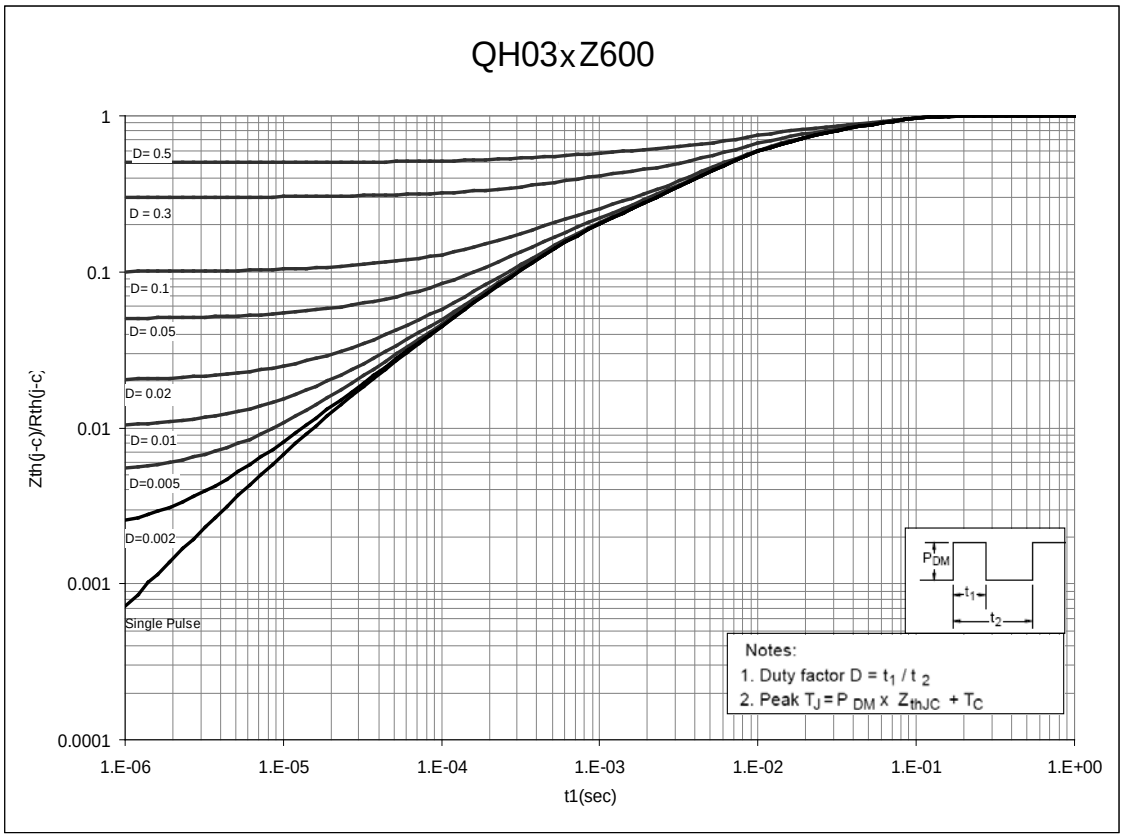
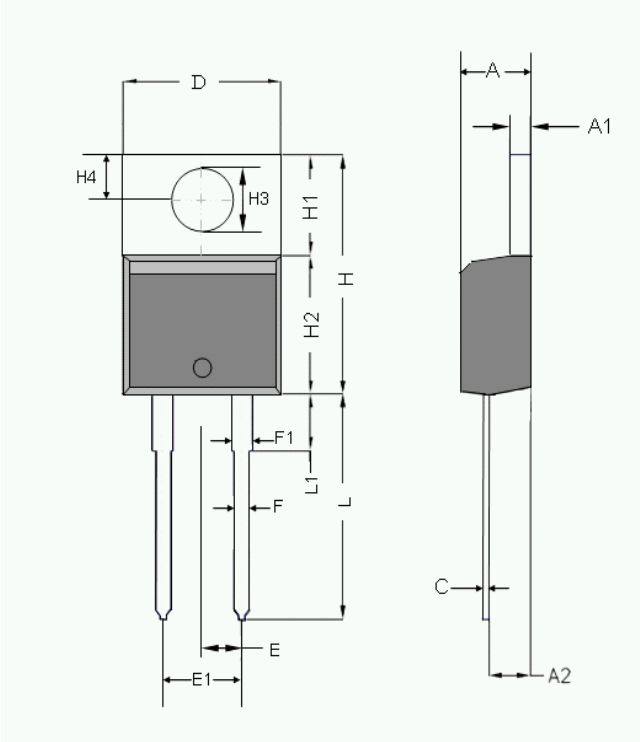


Figure 10. Normalized Maximum Transient Thermal Impedance.

Dimensional Outline Drawing

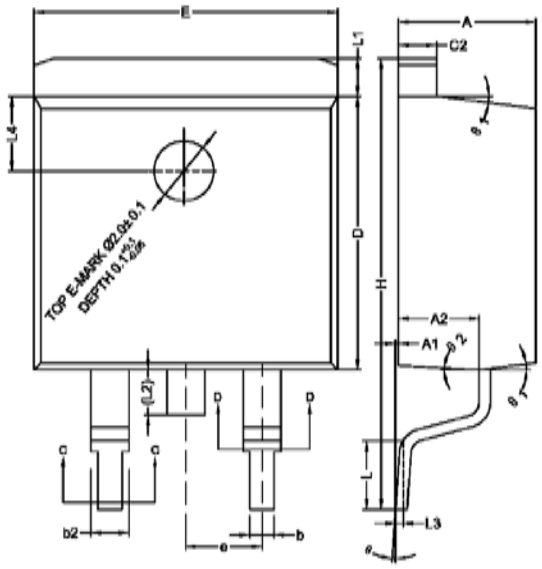
TO-220AC



	Millimeters	
Dim	**MIN**	**MAX**
A	4.32	4.70
A1	1.14	1.40
A2	2.03	2.79
C	0.34	0.610
D	9.65	10.67
E	2.49	2.59
E1	4.98	5.18
F	0.508	1.016
F1	1.14	1.78
H	14.71	16.51
H1	5.84	6.795
H2	8.40	9.00
H3	3.53	3.96
H4	2.54	3.05
L	12.70	14.22
L1	-	6.35

Dimensional Outline Drawing

TO-263AB

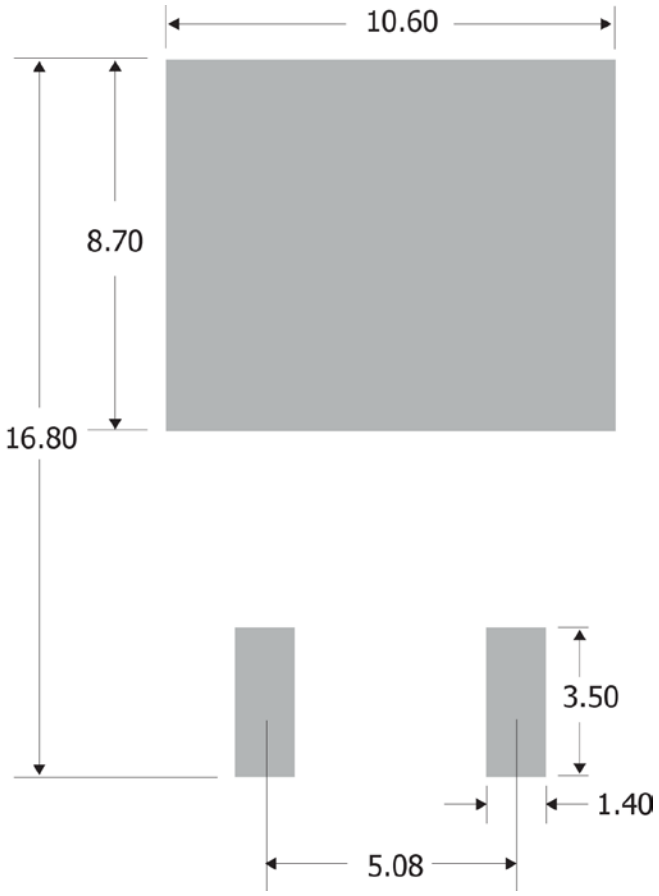


	Millimeters	
Dim	**MIN**	**MAX**
A	4.40	4.70
A1	0.00	0.25
A2	2.59	2.79
b	0.77	0.90
b2	1.23	1.36
c2	1.22	1.32
D	9.05	9.25
E	10.06	10.26
e	2.54 BSC	2.54 BSC
H	14.70	15.50
L	2.00	2.60
L1	1.17	1.40
L2	–	1.75
L3	0.25 BSC	0.25 BSC
L4	2.00 BSC	2.00 BSC
Θ	0°	8°
Θ1	5°	9°
Θ2	1°	5°

Mechanical Mounting Method	Maximum Torque / Pressure specification
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)
Clamp against package body	12.3 kilogram-force per square centimeter (kgf/cm^2) or 175 lbf/in^2

Footprint and Solder Pad Dimensions

Pad Dimensions in mm:
TO-263AB



Soldering time and temperature: This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

Ordering Information

Part Number	Package	Packing
QH03TZ600	TO-220AB	50 units/tube
QH03BZ600	TO-263AB	800 units/reel

The information contained in this document is subject to change without notice**.**

Revision	Notes	Date
1.0	Released by Qspeed	01/10
1.1	Converted to Power Integrations Document	01/11
1.2	Added QH03BZ600	02/13
1.3	Updated with new Brand Style. Added footprint and solder pad dimension for TO-263AB package.	11/15

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Power Integrations Worldwide Sales Support Locations

WORLD HEADQUARTERS
5245 Hellyer Avenue
San Jose, CA 95138, USA.
Main: +1-408-414-9200
Customer Service:
Phone: +1-408-414-9665
Fax: +1-408-414-9765
e-mail: usasales@power.com

GERMANY
Lindwurmstrasse 114
80337, Munich
Germany
Phone: +49-895-527-39110
Fax: +49-895-527-39200
e-mail: eurosales@power.com

JAPAN
Kosei Dai-3 Building
2-12-11, Shin-Yokohama,
Kohoku-ku
Yokohama-shi, Kanagawa
222-0033 Japan
Phone: +81-45-471-1021
Fax: +81-45-471-3717
e-mail: japansales@power.com

TAIWAN
5F, No. 318, Nei Hu Rd.,
Sec. 1
Nei Hu District
Taipei 11493, Taiwan R.O.C.
Phone: +886-2-2659-4570
Fax: +886-2-2659-4550
e-mail: taiwansales@power.com

CHINA (SHANGHAI)
Rm 2410, Charity Plaza, No. 88,
North Caoxi Road,
Shanghai, PRC 200030
Phone: +86-21-6354-6323
Fax: +86-21-6354-6325
e-mail: chinasales@power.com

INDIA
#1, 14th Main Road
Vasanthanagar
Bangalore-560052
India
Phone: +91-80-4113-8020
Fax: +91-80-4113-8023
e-mail: indiasales@power.com

KOREA
RM 602, 6FL
Korea City Air Terminal B/D,
159-6
Samsung-Dong, Kangnam-Gu,
Seoul, 135-728 Korea
Phone: +82-2-2016-6610
Fax: +82-2-2016-6630
e-mail: koreasales@power.com

UK
Cambridge Semiconductor,
a Power Integrations company
Westbrook Centre, Block 5,
2nd Floor
Milton Road
Cambridge CB4 1YG
Phone: +44 (0) 1223-446483
e-mail: eurosales@power.com

CHINA (SHENZHEN)
17/F, Hivac Building, No. 2, Keji
Nan 8th Road, Nanshan District,
Shenzhen, China, 518057
Phone: +86-755-8672-8689
Fax: +86-755-8672-8690
e-mail: chinasales@power.com

ITALY
Via Milanese 20, 3rd. Fl.
20099 Sesto San Giovanni
(MI) Italy
Phone: +39-024-550-8701
Fax: +39-028-928-6009
e-mail: eurosales@power.com

SINGAPORE
51 Newton Road,
#19-01/05 Goldhill Plaza
Singapore, 308900
Phone: +65-6358-2160
Fax: +65-6358-2015
e-mail: singaporesales@power.com